



## Analog Mixed Signal

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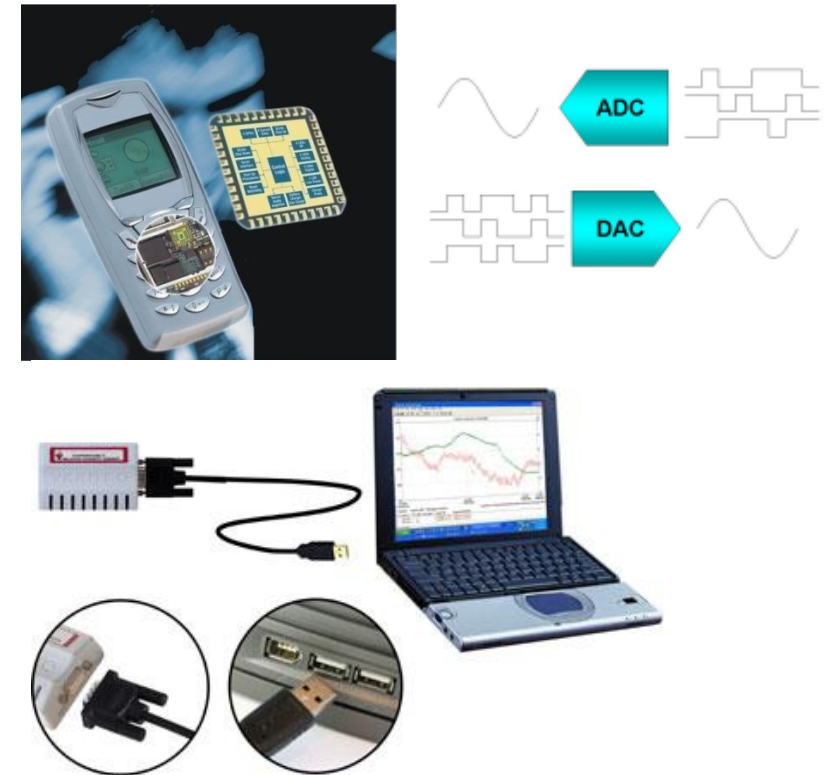


# Agenda

- Introduction
- Capabilities
- Case Study
- Profile - Offshore Manager

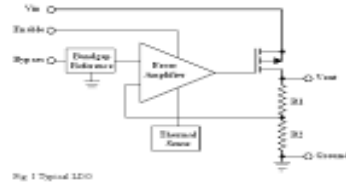
# Introduction

- Analog team lead by highly professional technologists with 50+ years of cumulative industry experience in designing chips for Analog stream of IC design.
- Analog experience, mainly into Power Management
- Also have experience in Signal Processing (converters, Serdes)
- We provide onsite, offsite and offshore technology solutions for all Analog IC design needs.
- In Past we have worked with TSMC, Renesas, NEC, Hitachi-ULSI
- We can provide end to end services comprising front end and back end design(Spec to Silicon).



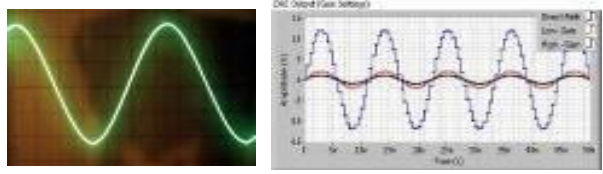
# AMS - Capability snapshot

## Power Management Circuits



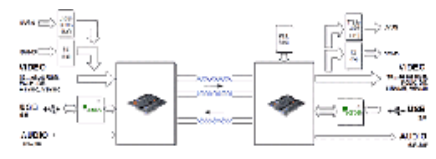
- Linear & Switching Regulators
- Reference & Protection Circuits
- Charge Pump
- Temp Sensors

## Analog Signal Processing



- A/D Converters
- D/A Converters
- Signal Conditioning
- Filters & Amplifiers

## High-speed Comm Interfaces



- High Speed I/O
- Serial Interface
- Clock Circuits

## Analog Modeling & Verification

- Technology Porting : 3 categories

- Circuit Design, Simulation & Analysis
- Block & Full chip Layout,
- IO design & layout

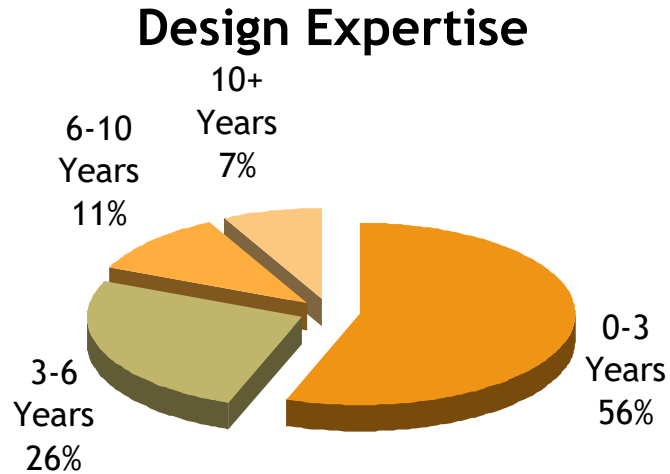
- Modeling & Mixed Signal Verification
- Parasitic Extraction

- Post silicon
- Bench bring-up & testing

# AMS Experience Overview

**Team Size**  
25+

## Process Experience







Technology*	Variants
45nm to .45u CMOS	<ul style="list-style-type: none"> <li>• High Speed &amp; Low Power for Analog and Custom Digital blocks</li> <li>• Supply voltages &lt; 1V</li> </ul>
0.45u, 0.32μ, 0.15μ	<ul style="list-style-type: none"> <li>• High voltage CMOS (~15V)</li> </ul>
45nm, 65nm, 90nm, 130nm, 150nm	<ul style="list-style-type: none"> <li>• Generic process</li> <li>• High speed</li> <li>• Low leakage</li> <li>• High voltage variants</li> </ul>
0.18μ, 0.15μ, 0.13μ	<ul style="list-style-type: none"> <li>• RFCMOS process</li> </ul>

\* Includes proprietary process expertise

# Analog & Mixed Signal : Quality Process

- Engineering Process for AMS work flows
  - System Model Development Process “System-Model-Development-Process”
  - Analog Circuit Design Process “Analog Circuit Design”
  - Layout Design Process “Layout-Design-Process”
- Comprehensive Checklists for tracking the various phases of the project
- Strict Peer and Multilevel Reviews
- Detailed and Live Know-how document for all Projects
- Knowledge sharing Repository

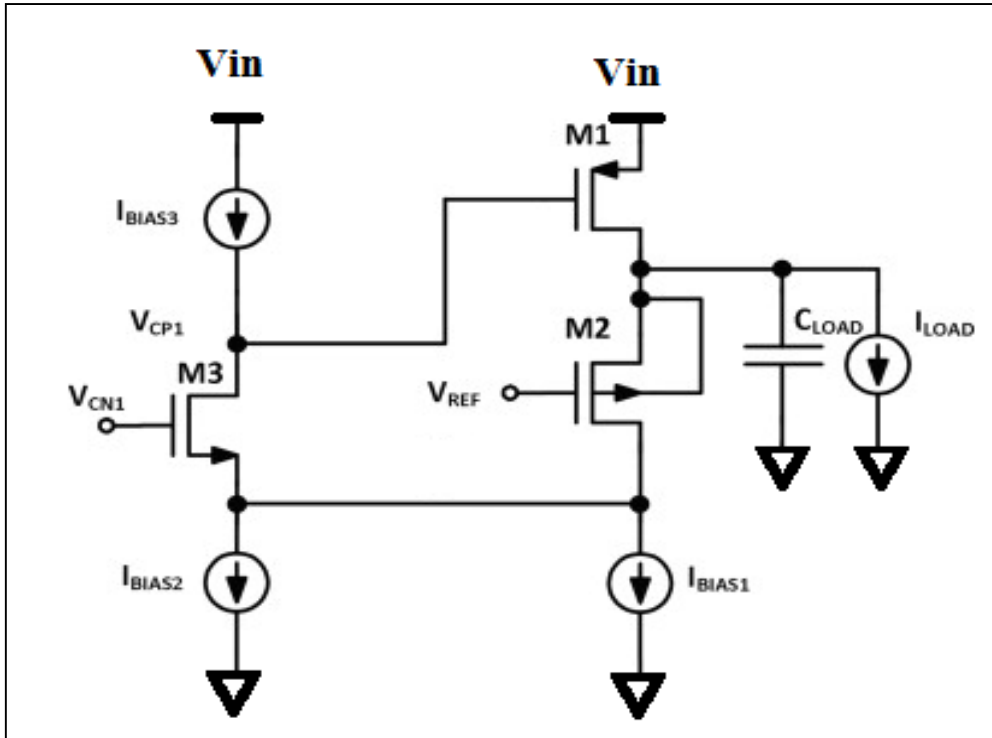
Engineering Process documents specific to AMS Practice are attached below :

 Analog Circuit design	 Layout Design Process	 System Model Development Process	 AMS_IO_LayoutDes ign_Process.doc
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- Case Study
  - Power Management
  - Converters
  - I/O

# Capacitor-less LDO

- Capacitor less LDO for low load current Point of Load (POL) application



Foundry : TSMC

Process : 40nm

Load current : 10mA ; Input Voltage : 1.6 to 3.6V

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- Features

***Low Power SOCs requires many blocks to be turned OFF during power saving modes. Hence there is a need for multiple, Point of Load (POL) Capacitor less LDOs.***

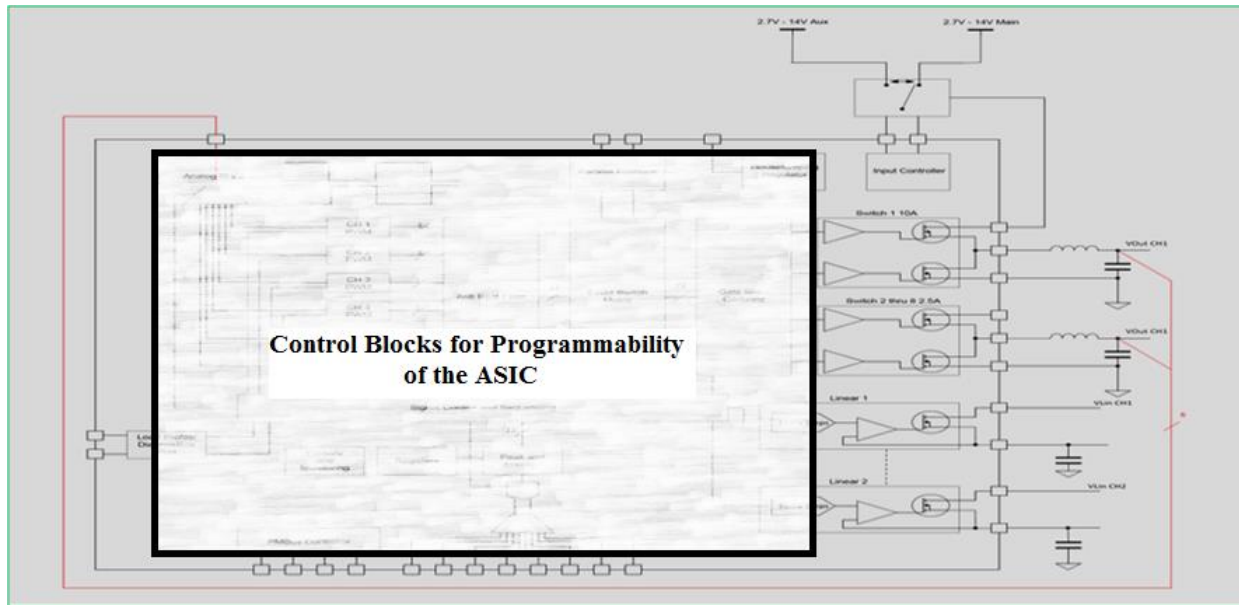
***The architecture of the LDO will remain same but output voltage and load current remains different for every instance of LDO in the SOC***

- Low in area. 0.02mm sq.



# DC-DC Converter

- Programmable Multi-rail DC-DC converter



Foundry : Dongbu

Process : 180nm BCDMOS

Load current: 20A ; Output Voltage: 1V (programmable)

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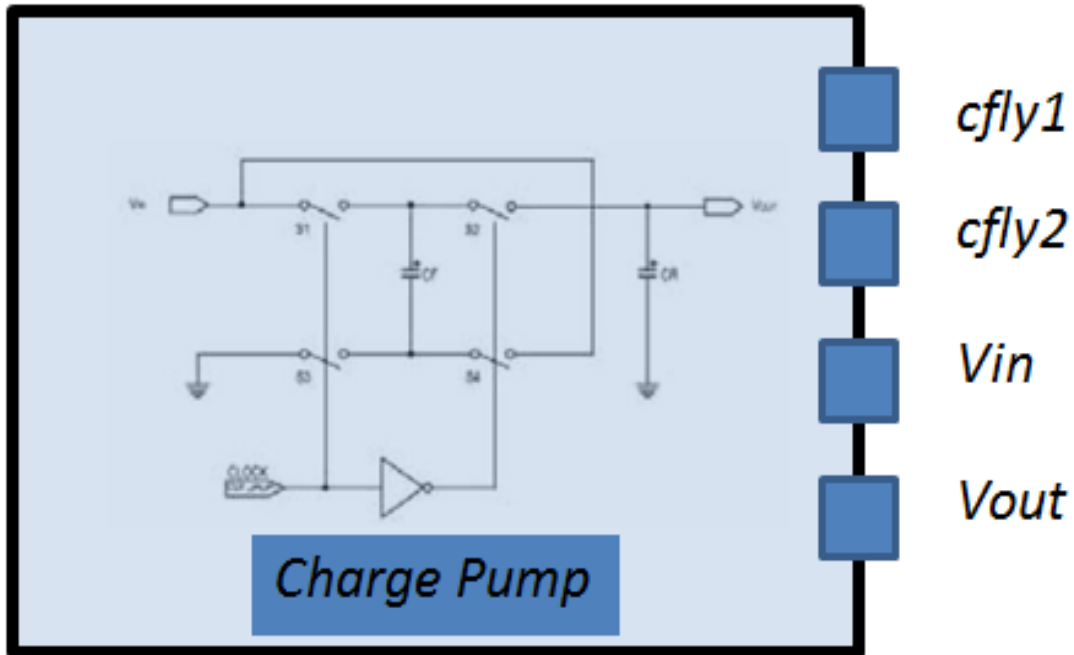
- Features

*This innovative single IC addresses applications which need multiple power rails. It comes with a novel idea of programmable output parameters like rail voltage, load current, switching frequency etc which is one of its kind in this industry.*

- Highly programmable. Output voltage programmable in steps of 20mV.
- Very high current. Also programmable in by adding 2A switches.

# Voltage Doubler

- Charge Pump Voltage Doubler



- Features

- CP10V:

- Charge pump Doubler
    - Input voltage is 5V and Output voltage ~10V
    - Soft start circuit has been implemented
    - Load current 10mA

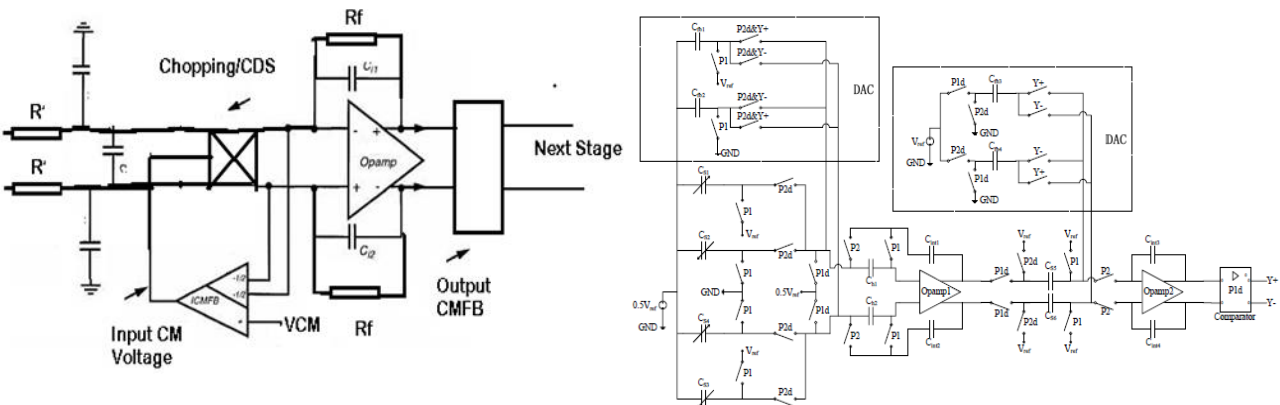
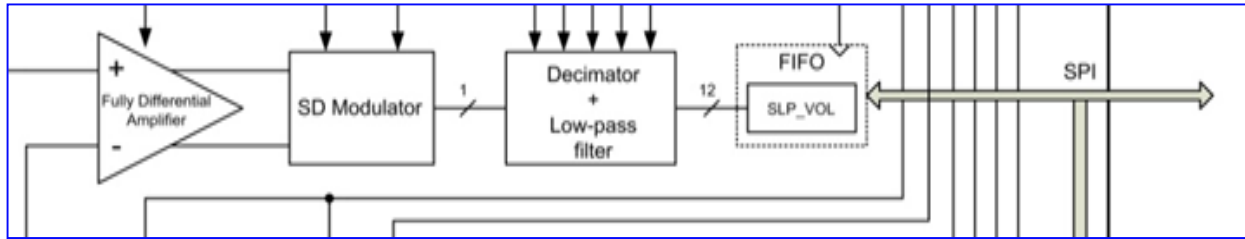
- Output resistance of 2Ω.
- Unregulated charge pump.
- Clock frequency of 500KHz.

Foundry : Korean pure play

Process : 180nm BCDMOS

Application: Hand held Gaming console

- Sigma Delta ADC



Fab: Custom client process

Tools: Cadence Virtuoso & Matlab

Applications: Automotive for position measurement.

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## High level specs

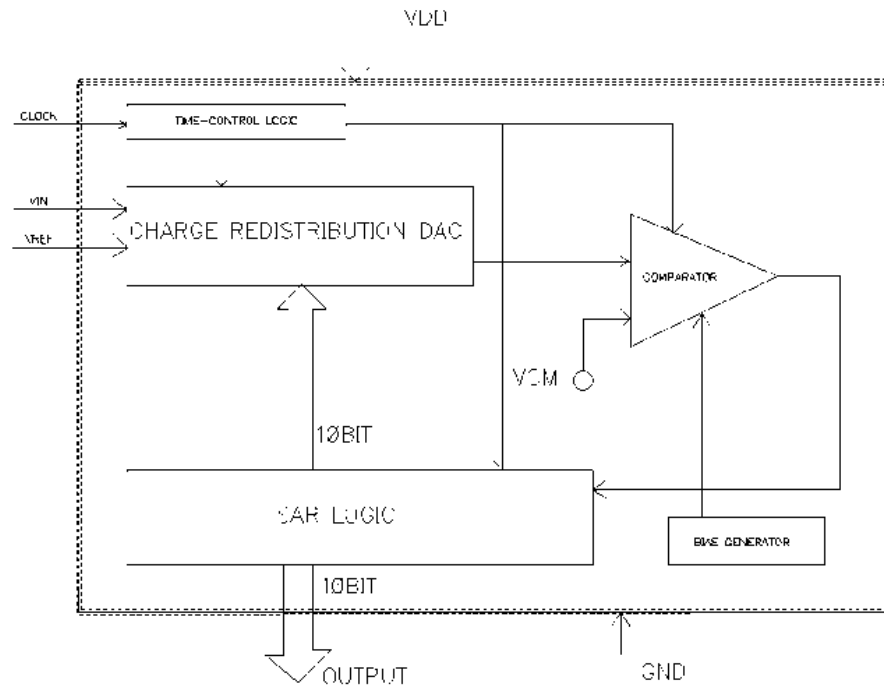
- Process Node 65nm
- Signal Bandwidth 2.4kHz
- Oversampling Ratio 1024
- Sampling frequency 5.28MHz
- SNDR (approximate) Min 100dB
- Resolution 12Bits after range conversion
- Temp range -40°C to 140°C

## • Challenge:

- The Area, Power and Speed specifications of this IC, targeted for Consumer application, was challenging

## Description

- 10-Bit, 2.0 MSPS SAR ADC



Fab: Custom client process

Tools: Cadence Virtuoso & Matlab

Applications: Automotive for position measurement.

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## High level specs

- Fully Capacitive, Segmented Charge redistribution DAC
- 3 Stage auto-zeroed Comparator
- DAC Capacitors re-used for I/P Sampling

## Scope

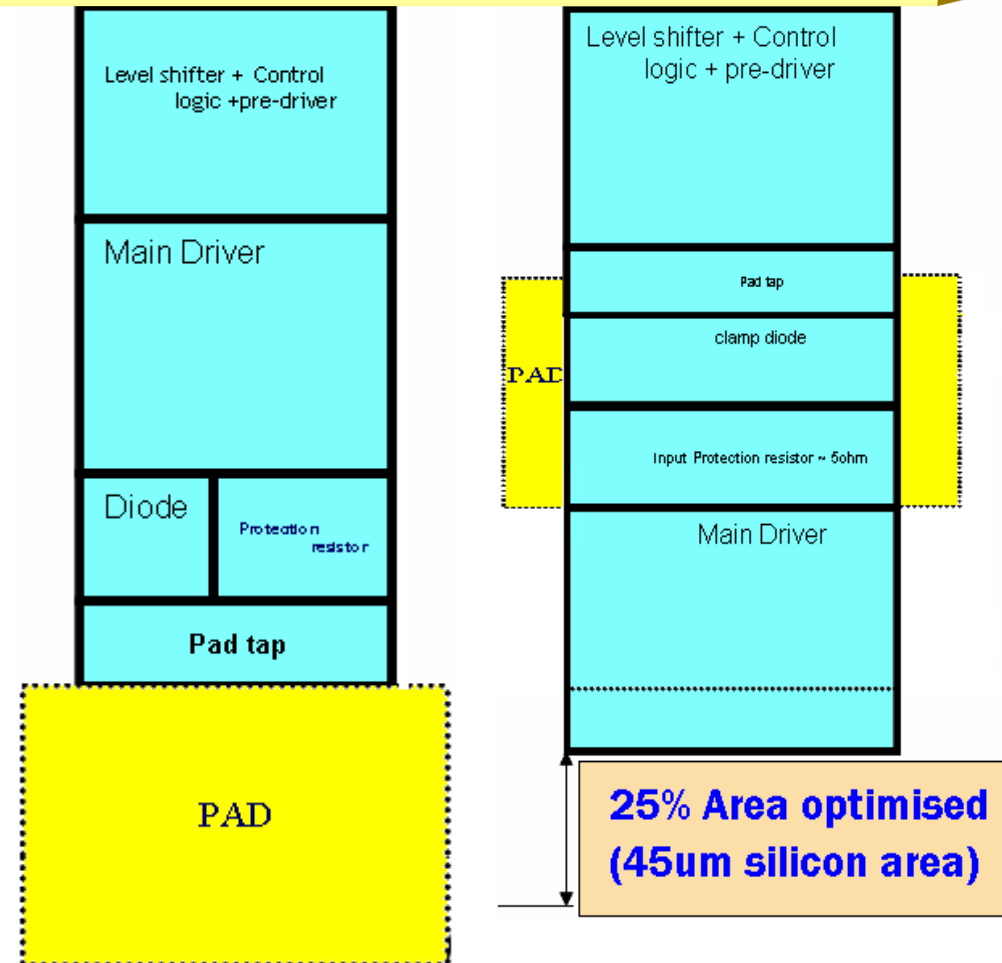
- Architecture study & Feasibility analysis using Verilog-A and MATLAB
- Schematic design
- Circuit simulations & characterization
- Layout design and Physical Verification
- Extraction and Post RC Simulations
- Post silicon testing and validation

- Highlight:

# I/O Case Studies: Migration

## Migration

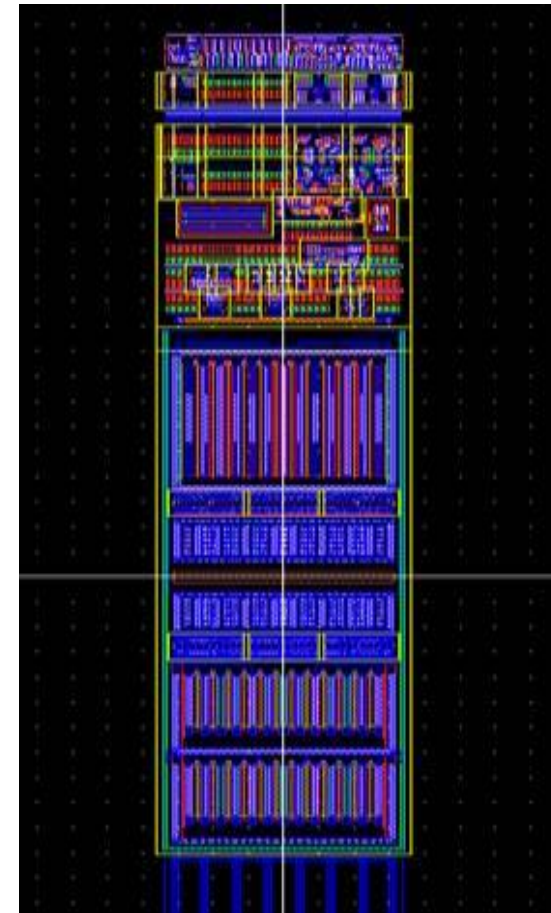
- Process Migration
  - Have completed numerous projects
  - Have migrated the whole IO libraries from 130nm to 90nm and 65nm
  - Have migrated from 'G' process to 'LP' process
- Layout migration
  - Have changed the IO cell layouts from 'non-PAD on IO' to 'PAD on IO' for various process (90nm, 65nm, etc)



# I/O Case Studies: std CMOS IO library development

Spec to GDSII : std CMOS IO library

- Development of ~ 150 IO cells
  - Duration: 3 calendar months
  - Team size: 3
  - Process: TSMC 65nm
  - IO cells have different drivability, slew rate control options
  - IO cells include Bi-directional, Input, Output, open drain
  - Our tasks included design, layout (Pad on IO), verification, post-layout validation, combinational verification
  - Simulations include VOH/VOL, VIH/VIL, di/dt, leakage, delay, Tr/Tf, functional
  - Tools used: CADENCE, HSPICE, Calibre, Columbus-AMS, HSIM



# Full chip Layout projects

- ❑ *Ultra high current LDO*
  - *Load current : 3A*
  - *Chip size: 2.1 mm X 2.5 mm*
  - *Process: 0.35um BCDMOS*
  - *Foundry : Korean pure play*
  
- ❑ *BLDC Fan Motor Drivers*
  - *Supply Voltages: 15V, 28V & 50V*
  - *Chip size: 2.0 mm X 2.1 mm, 2.8mm X 3 mm*
  - *Process: 0.35um BCDMOS*
  - *Foundry : Proprietary Process*
  
- ❑ *DC DC Buck Converter IC – 2 instances*
  - *Load current : 3A*
  - *Chip size: 5.0 mm X 5.0 mm*
  - *Process: 0.18um BCDMOS*
  - *Foundry : TSMC*

Thank You

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